

Amendment to Specification

Please insert the following text on page 6 of the Specification immediately before the heading "Example of the initial growth":

FIG. 1 is a graph showing Reflectivity and Substrate Temperature as a Function of Time.

FIG. 2 is a graph showing PL spectrum obtained with the quintuple MQW GaInN/GaN deposited on the new initial growth stratum.

Please replace the text on page 7, lines 10-12, with the following amended text:

~~The development of the most important growth parameters (reactor temperature, reactor pressure, N₂, H₂, TMGa, TMI_n, TEGa flow) versus time is illustrated in graphic 3~~ The evaluation of the optical characteristics is presented in Table 1 Figure 2.

Please replace the text on page 7, lines 13-25, with the following amended text:

The distinction resides in the growth of the first nucleation layer on the substrate. In the known growth process the first nucleation layer is deposited at 530 °C under an N₂ atmosphere at 950 mbar for 8 minutes. The stratum presents cubic elements and is not coherent. Following the deposition of the stratum the growth is interrupted and heating is continued up to 1170 °C. Then a healing step is performed for 2 minutes. During this step re-crystallization from the cubic crystal phase to the hexagonal phase takes place. The growth of

the GaN buffer layer is then performed at 1160 °C. In the novel method of the present invention a continuous growth takes place during the step of heating from 530 °C to 1170 ° without any interruption of the growth and without any healing step which would permit re-crystallization. The growth therefore takes place in an H₂ atmosphere at 200 mbar. The comparison of the properties presented in ~~Table 1~~ Figure 2 reveals a higher light yield at a constant emission wavelength